# NSDEMN11XV6T1, NSDEMN11XV6T5

# **Common Cathode Quad Array Switching Diode**

This Common Cathode Epitaxial Planar Quad Diode is designed for use in ultra high speed switching applications. This device is housed in the SOT–563 package which is designed for low power surface mount applications, where board space is at a premium.

### Features

- Fast t<sub>rr</sub>
- Low C<sub>D</sub>
- Pb–Free Packages are Available

### **MAXIMUM RATINGS** ( $T_A = 25^{\circ}C$ )

Rating	Symbol	Value	Unit
Reverse Voltage	V <sub>R</sub>	80	Vdc
Peak Reverse Voltage	V <sub>RM</sub>	80	Vdc
Forward Current	١ <sub>F</sub>	100	mAdc
Peak Forward Current	I <sub>FM</sub>	300	mAdc
Peak Forward Surge Current	I <sub>FSM</sub> (Note 1)	2.0	Adc

### THERMAL CHARACTERISTICS

Characteristic (One Junction Heated)SymbolMaxUnitTotal Device Dissipation @TA = 25°CPD357 (Note 2) 2.9mW mW/°CDerate above 25°CPD350 (Note 2)mW/°CThermal Resistance, Junction-to-AmbientR $_{\theta JA}$ 350 (Note 2)°C/WCharacteristic (Both Junctions Heated)SymbolMaxUnitTotal Device Dissipation @TA = 25°CPD500 (Note 2)mW/°CDerate above 25°C4.0mW/°C				
Derate above 25°C(Note 2) 2.9 (Note 2)mW/°CThermal Resistance, Junction-to-Ambient $R_{\theta JA}$ $350$ (Note 2)°C/WCharacteristic (Both Junctions Heated)SymbolMaxUnitTotal Device Dissipation @TA = 25°C $P_D$ $500$ (Note 2)mW/°C		Symbol	Мах	Unit
Derate above 25°C2.9 (Note 2)mW/°CThermal Resistance, Junction-to-Ambient $R_{\theta JA}$ 350 (Note 2)°C/WCharacteristic (Both Junctions Heated)SymbolMaxUnitTotal Device Dissipation @TA = 25°CPD500 (Note 2)mW	Total Device Dissipation $@T_A = 25^{\circ}C$	PD		mW
Characteristic (Both Junctions Heated) Symbol Max Unit   Total Device Dissipation @T <sub>A</sub> = 25°C P <sub>D</sub> 500 (Note 2) mW	Derate above 25°C		`2.9 ´	mW/°C
(Both Junctions Heated)SymbolMaxUnitTotal Device Dissipation @TA = 25°CPD500 (Note 2)mW	Thermal Resistance, Junction-to-Ambient	$R_{\thetaJA}$		°C/W
Total Device Dissipation $@T_A = 25^{\circ}C$ P_D500 (Note 2)mW	Characteristic			
(Note 2)	(Both Junctions Heated)	Symbol	Max	Unit
	Total Device Dissipation $@T_A = 25^{\circ}C$	PD		mW
	Derate above 25°C		· · · ·	mW/⁰C
(Note 2)				
Thermal Resistance, Junction-to-Ambient $R_{\theta JA}$ 250 (Note 2)°C/W	Thermal Resistance, Junction-to-Ambient	$R_{\thetaJA}$		°C/W
Junction and Storage Temperature $T_J$ , $T_{stg}$ -55 to +150 °C				

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

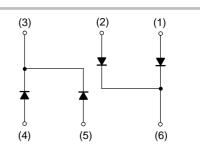
1. t = 1 μS

2. FR-4 @ Minimum Pad



# **ON Semiconductor®**

### http://onsemi.com





CASE 463A PLASTIC

## MARKING DIAGRAM



N9 = Specific Device Code M = Date Code = Pb-Free Package (Note: Microdot may be in either location)

### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
NSDEMN11XV6T1	SOT-563	4000/Tape & Reel
NSDEMN11XV6T1G	SOT-563 (Pb-Free)	4000/Tape & Reel
NSDEMN11XV6T5	SOT-563	8000/Tape & Reel
NSDEMN11XV6T5G	SOT-563 (Pb-Free)	8000/Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

## NSDEMN11XV6T1, NSDEMN11XV6T5

Characteristic	Symbol	Condition	Min	Max	Unit
Reverse Voltage Leakage Current	I <sub>R</sub>	V <sub>R</sub> = 70 V	-	0.1	μAdc
Forward Voltage	V <sub>F</sub>	I <sub>F</sub> = 100 mA	-	1.2	Vdc
Reverse Breakdown Voltage	V <sub>R</sub>	I <sub>R</sub> = 100 μA	80	-	Vdc
Diode Capacitance	CD	V <sub>R</sub> = 6.0 V, f = 1.0 MHz	-	3.5	pF
Reverse Recovery Time	t <sub>rr</sub> (Note 3)	$I_F = 5.0 \text{ mA}, V_R = 6.0 \text{ V}, R_L = 100 \Omega, I_{rr} = 0.1 I_R$	-	4.0	ns

### **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C)

3. t<sub>rr</sub> Test Circuit on following page.

## TYPICAL ELECTRICAL CHARACTERISTICS

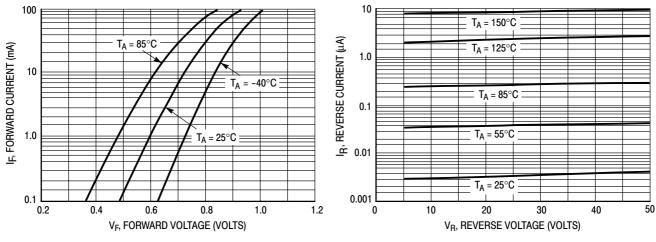


Figure 1. Forward Voltage

Figure 2. Reverse Current

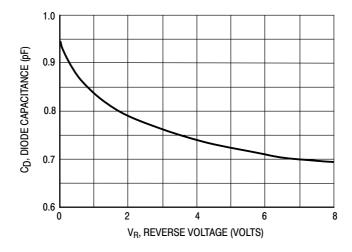


Figure 3. Diode Capacitance

# NSDEMN11XV6T1, NSDEMN11XV6T5

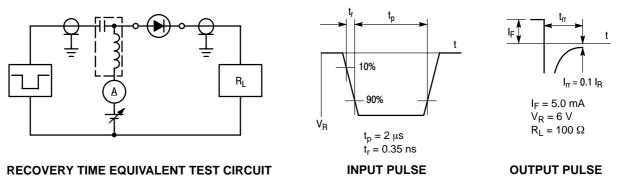
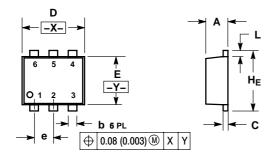


Figure 4. Reverse Recovery Time Test Circuit for the NSDEMN11XV6T1

### NSDEMN11XV6T1, NSDEMN11XV6T5

### PACKAGE DIMENSIONS

SOT-563, 6 LEAD CASE 463A-01 ISSUE F



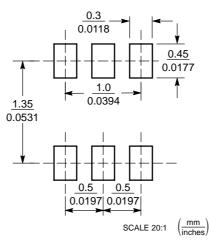
NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

CONTROLLING DIMENSION: MILLIMETERS 2

MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS 3. IS THE MINIMUM THICKNESS OF BASE MATERIAL.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.50	0.55	0.60	0.020	0.021	0.023
b	0.17	0.22	0.27	0.007	0.009	0.011
С	0.08	0.12	0.18	0.003	0.005	0.007
D	1.50	1.60	1.70	0.059	0.062	0.066
Е	1.10	1.20	1.30	0.043	0.047	0.051
е	0.5 BSC		0.02 BSC			
L	0.10	0.20	0.30	0.004	0.008	0.012
HE	1.50	1.60	1.70	0.059	0.062	0.066

#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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